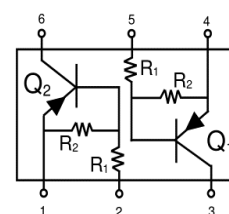
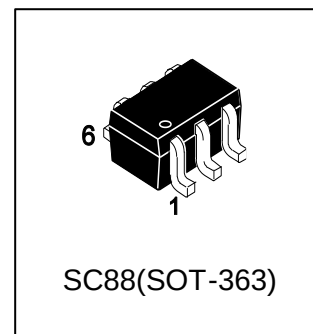


LMUN5111DW1T1G

Dual Bias Resistor Transistors
PNP Silicon Surface Mount Transistors
with Monolithic Bias Resistor Network



1. FEATURES

- Simplifies circuit design
- Reduces board space.
- Reduces Component Count
- Available in 8 mm, 7 inch/3000 Unit Tape and Reel
- We declare that the material of product compliance with RoHS requirements and Halogen Free.

2. DEVICE MARKING AND RESISTOR VALUES

Device	Marking	R1(K)	R2(K)	VIN (V)	Shipping
LMUN5111DW1T1G	0A	10	10	-40~+10	3000/Tape&Reel
LMUN5111DW1T3G	0A	10	10	-40~+10	13000/Tape&Reel

3. MAXIMUM RATINGS(Ta = 25°C)

Parameter	Symbol	Limits	Unit
Collector–Emitter Voltage	VCEO	-50	V
Collector–Base Voltage	VCBO	-50	V
Collector Current — Continuous	IC	-100	mA
Junction temperature	TJ	-55~+150	°C
Storage temperature	Tstg	-55~+150	°C

4. THERMAL CHARACTERISTICS

Parameter	Symbol	Limits	Unit
Total Device Dissipation, FR-4 Board (Note 1) @ TA = 25°C Derate above 25°C	PD	275 2.2	mW mW/°C
Thermal Resistance, Junction–to–Ambient(Note 1)	RθJA	454	°C/W
Thermal Resistance, Junction–to–Case	RθJC	192	°C/W

1. 30.0mm×25.0mm×1.6mm(FR4), Copper foil thickness 35μm;

5. ELECTRICAL CHARACTERISTICS (Ta= 25°C)

OFF CHARACTERISTICS

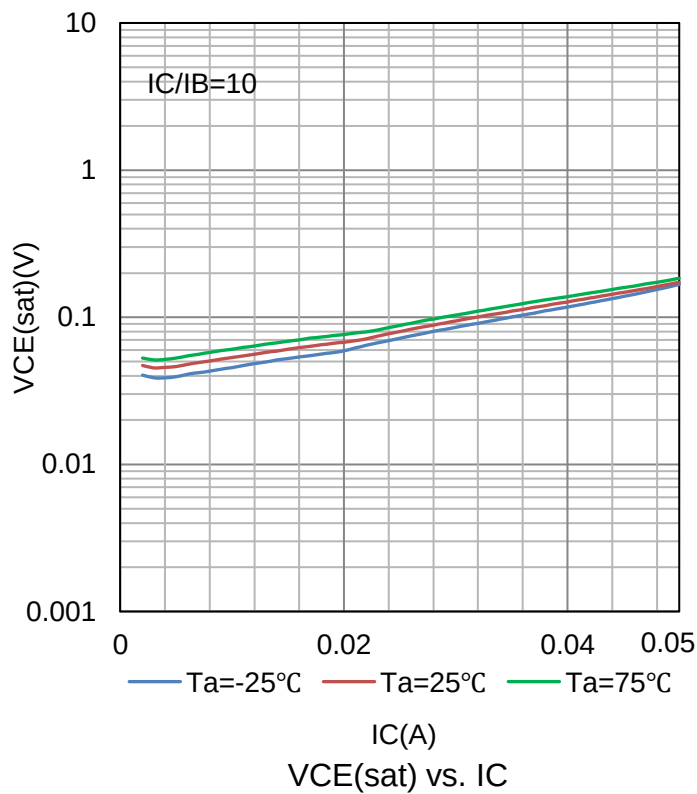
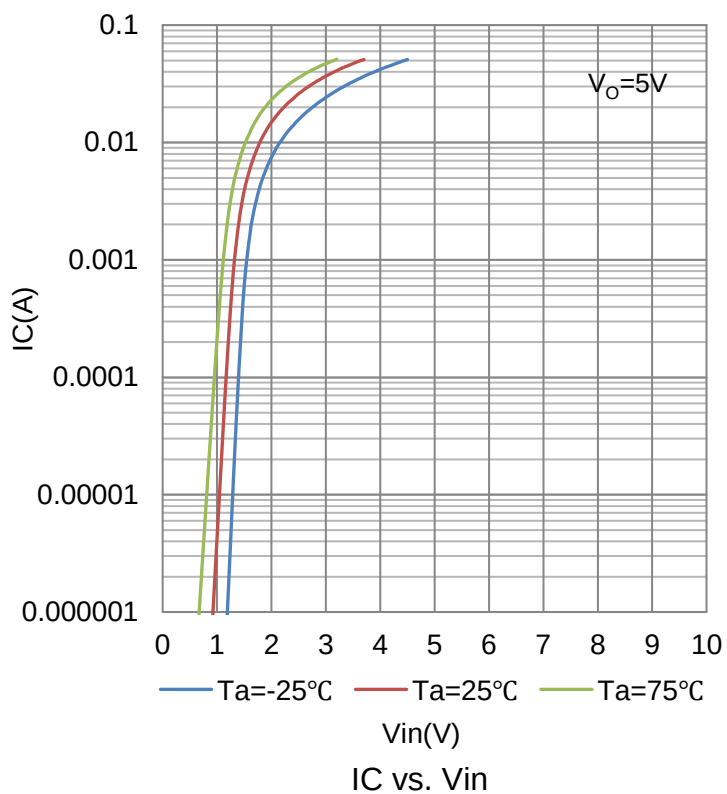
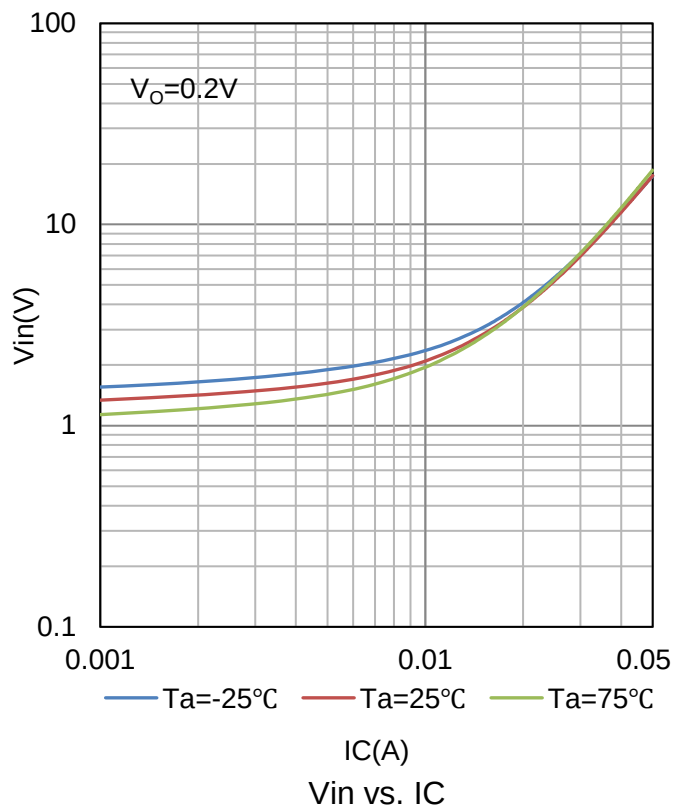
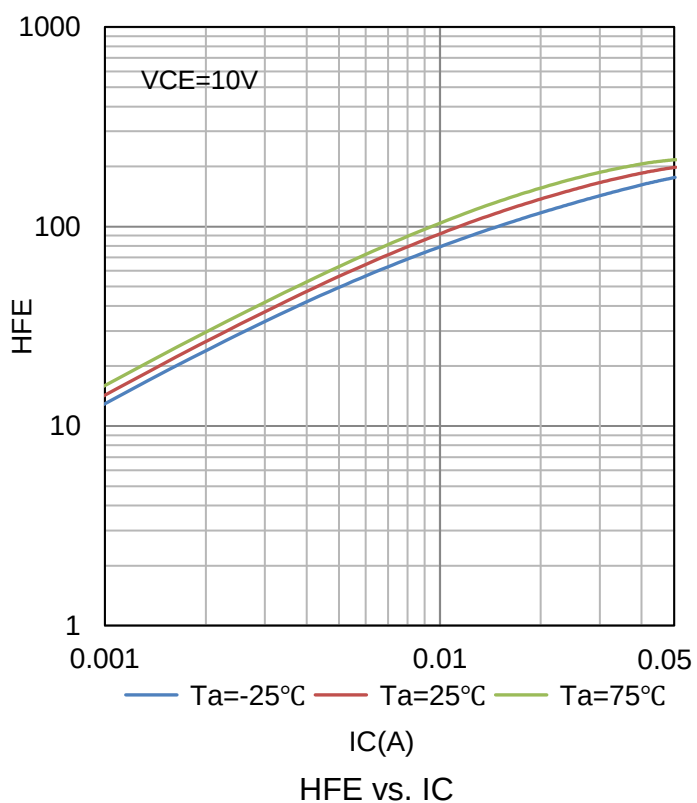
Characteristic	Symbol	Min.	Typ.	Max.	Unit
Collector–Emitter Breakdown Voltage (IC = -2.0 mA, IB = 0)	VBR(CEO)	-50	-	-	V
Collector–Base Breakdown Voltage (IC = -10 μ A, IE = 0)	VBR(CBO)	-50	-	-	V
Collector-Base Cutoff Current (VCB = -50 V, IE = 0)	ICBO	-	-	-100	nA
Collector-Emitter Cutoff Current (VCE = -50 V, IB = 0)	ICEO	-	-	-500	nA
Emitter-Base Cutoff Current (VEB = -6.0 V, IC = 0)	IEBO	-	-	-0.5	mA

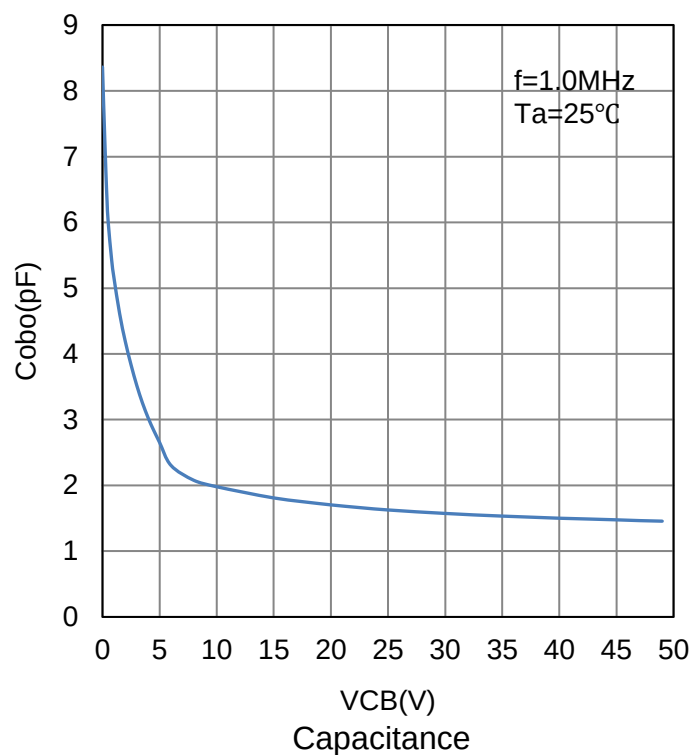
ON CHARACTERISTICS (Note 2.)

DC Current Gain (IC = -5.0 mA, VCE = -10 V)	HFE	35	60	-	
Collector–Emitter Saturation Voltage (IC = -10 mA, IB = -0.3 mA)	VCE(sat)	-	-	-0.25	V
On-State Input Voltage (VCE=-0.3V, IC=-10mA)	VI(on)	-3	-	-	V
Off-State Input Voltage (VCE=-5V, IC=-0.1mA)	VI(off)	-	-	-0.5	V
Output Voltage (on) (VCC = -5.0 V, VB = -2.5 V, RL = 1.0 k Ω)	VOL	-	-	-0.2	V
Output Voltage (off) (VCC = -5.0 V, VB = -0.5 V, RL =1.0K Ω)	VOH	-4.9	-	-	V
Input Resistor	R1	7	10	13	K Ω
Resistor Ratio	R1/R2	0.8	1	1.2	

2. Pulse Test: Pulse Width < 300 μ s, Duty Cycle < 2.0%

6.ELECTRICAL CHARACTERISTICS CURVES

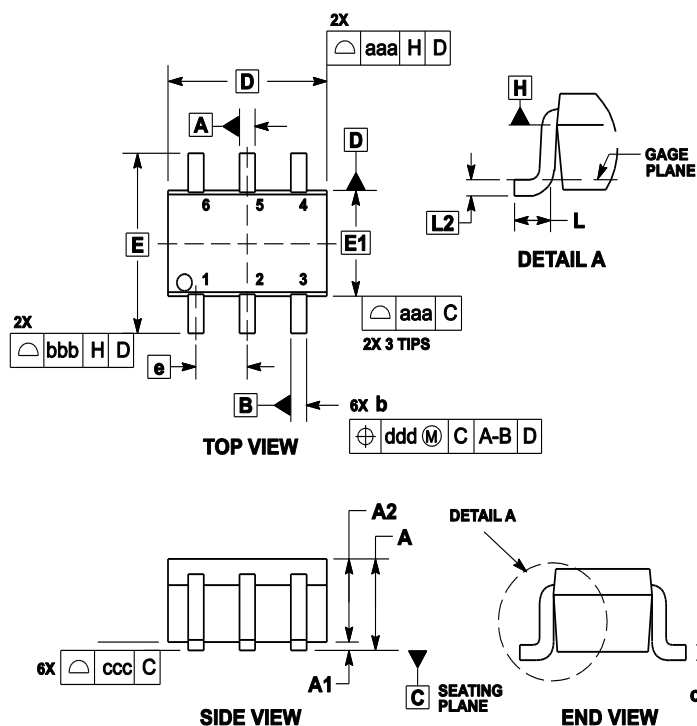


6.ELECTRICAL CHARACTERISTICS CURVES(Con.)

7.OUTLINE AND DIMENSIONS

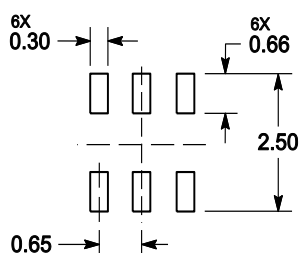
Notes:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.



DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	---	---	1.10	---	---	0.043
A1	0.00	---	0.10	0	---	0.004
A2	0.70	0.90	1.00	0.027	0.035	0.039
b	0.15	0.20	0.25	0.006	0.008	0.01
C	0.08	0.15	0.22	0.003	0.006	0.009
D	1.80	2.00	2.20	0.07	0.078	0.086
E	2.00	2.10	2.20	0.078	0.082	0.086
E1	1.15	1.25	1.35	0.045	0.049	0.053
e	0.65 BSC			0.026 BSC		
L	0.26	0.36	0.46	0.010	0.014	0.018
L2	0.15 BSC			0.006 BSC		
aaa	0.15			0.01		
bbb	0.30			0.01		
ccc	0.10			0.00		
ddd	0.10			0.00		

8.SOLDERING FOOTPRINT



DISCLAIMER

- Curve guarantee in the specification. The curve of test items with electric parameter is used as quality guarantee. The curve of test items without electric parameter is used as reference only.
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